

# 1015MP

15 Watts, 50 Volts Avionics 1025 - 1150 MHz

## **GENERAL DESCRIPTION**

The 1015 MP is a COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 1025-1150 MHz. The device has gold thin-film metallization for proven highest MTTF. The transistor includes input prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.

## **CASE OUTLINE** 55FW-1

## **ABSOLUTE MAXIMUM RATINGS**

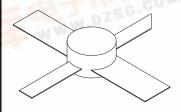
Maximum Power Dissipation @ 25°C<sup>2</sup> 50 Watts Pk

**Maximum Voltage and Current** 

65 Volts BVces Collector to Emitter Voltage **BVebo** Emitter to Base Voltage 3.5 Volts Ic Collector Current 1.0 Amps Pk

**Maximum Temperatures** 

Storage Temperature  $-65 \text{ to} + 150^{\circ}\text{C}$ Operating Junction Temperature  $+200^{\circ}C$ 



## **ELECTRICAL CHARACTERISTICS @ 25°C**

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P <sub>OUT</sub>	Power Out	F= 1025-1150 MHz	15	MAG		W
$P_{IN}$	Power Input	Vcc = 50 Volts			1.5	W
$P_{G}$	Power Gain	$PW = 10 \mu sec, DF = 1\%$	10	11		dB
ης	Efficiency	COM		40		%
VSWR	Load Mismatch Tolerance	F = 1090 MHz			20:1	

## FUNCTIONAL CHARACTERISTICS @ 25°C

BVebo	Emitter to Base Breakdown	Ie = 5  mA	3.5			V
BVces	Collector to Emitter Breakdown	Ic = 15mA	65	2-4	W	V
Hfe	DC Current Gain	Vce = 5V, Ic = 100  mA	20	Tu W	072	
Cob	Output Capacitance	Vcb = 50 V, f = 1 MHz	- T- '	5.0	7.5	pF
θjc <sup>2</sup>	Thermal Resistance				3.5	°C/W

Note 1: At rated output power and pulse conditions WWW.DZEG.GOA

2: At rated pulse conditions

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